

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2003-331855

(43)Date of publication of application : 21.11.2003

(51)Int.Cl.

H01M 4/90

H01M 4/88

H01M 8/10

(21)Application number : 2002-141103

(71)Applicant : TOKYO INST OF TECHNOL

(22)Date of filing : 16.05.2002

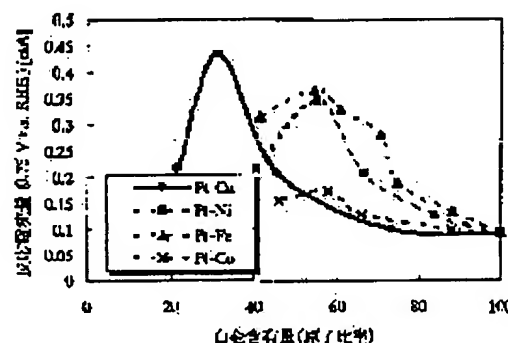
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## (54) CATHODE CATALYST FOR SOLID POLYMER FUEL CELL AND SOLID POLYMER FUEL CELL

(57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a cathode catalyst for a solid polymer electrolyte fuel cell substantially reducing the amount of Pt used, and realizing remarkably high activity, and to provide a solid polymer fuel cell.

**SOLUTION:** This cathode catalyst for the solid polymer fuel cell is formed by retaining a Pt-Cu base alloy on conductive carbon. The Pt-Cu base alloy contains 20-40% Pt in the ratio of the number of atoms as a composition ratio. The Pt-Cu base alloy is a Pt-Cu alloy having Pt:Cu=3:7 in the ratio of the number of atoms as the composition ratio. The Pt-Cu base alloy is retained on the conductive carbon by high frequency sputtering.



## LEGAL STATUS

[Date of request for examination] 16.05.2002

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

# EUROPEAN PATENT OFFICE

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## Patent Abstracts of Japan

PUBLICATION NUMBER : 08100255  
PUBLICATION DATE : 16-04-96

APPLICATION DATE : 30-09-94  
APPLICATION NUMBER : 06261229

APPLICANT : MITSUBISHI MATERIALS CORP;

INVENTOR : KINOSHITA MAKOTO;

INT.CL. : C23C 14/34 C22C 21/00 H01L 29/40 H01L 29/43

TITLE : SPUTTERING TARGET MATERIAL FOR FORMING THIN FILM OF THIN FILM TRANSISTOR

ABSTRACT : PURPOSE: To obtain a sputtering target material generating a small number of particles and capable of forming a thin film less liable to cause unevenness in the alloying component content with the lapse of time.

CONSTITUTION: This sputtering target material has a compsn. consisting of 1-20wt.% one or more kinds of alloying components selected from among Nb, V, Ti, Zr, Ni, Pt and W and the balance Al with inevitable impurities and a recrystallized structure contg. an intermetallic compd. of Al with the alloying components dispersed as particles of  $\leq 30\mu\text{m}$  average particle diameter in the matrix of  $\leq 30\mu\text{m}$  average grain diameter. This target material can suppress the generation of particles during film formation.

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